

自主封測 品質把控 售後保障

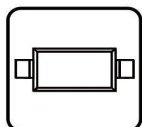
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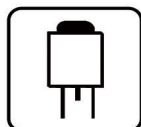
電源管理



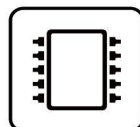
顯示驅動



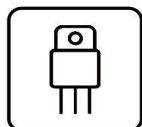
二三極管



LDO穩壓器



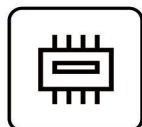
觸摸芯片



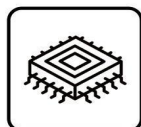
MOS管



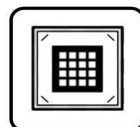
運算放大器



存儲芯片



MCU



串口通信

SS8050 Y1-TD(0.52)

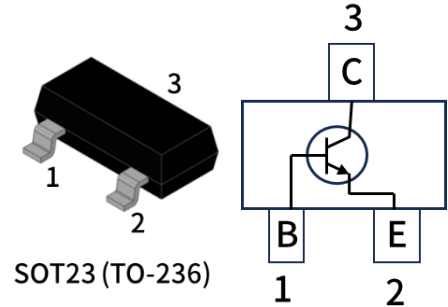
產品規格說明書

SS8050LST1

General Purpose Transistors NPN

1. FEATURES

- The material of product compliance with RoHS requirements and Halogen Free.
- High Stability and High Reliability.
- Complementary to SS8550LST1 (PNP).
- High current capacity in compact package. $I_C = 1.5\text{ A}$.



2. Mechanical Data

- SOT-23 Small Outline Plastic Package.
- Tin plated leads, solderable per J-STD-002 and JESD22-B102.
- Marking: Y1

3. ORDERING INFORMATION

Device	Min Pack	Inner Box	Outer Carton	Reel
SS8050LST1	3000	45000	180000	7 inch

4. MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Limit	Unit
Collector-Emitter Voltage	V_{CE0}	25	V
Collector-Base Voltage	V_{CB0}	40	V
Emitter-Base Voltage	V_{EB0}	5	V
Collector Current--Continuous	I_C	1.5	A
Collector Power Dissipation	P_C	300	mW

5. THERMAL CHARACTERISTICS

Parameter	Symbol	Limit	Unit
Operation Junction and Storage Temperature Range	TSTG	-55~150	$^\circ\text{C}$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$

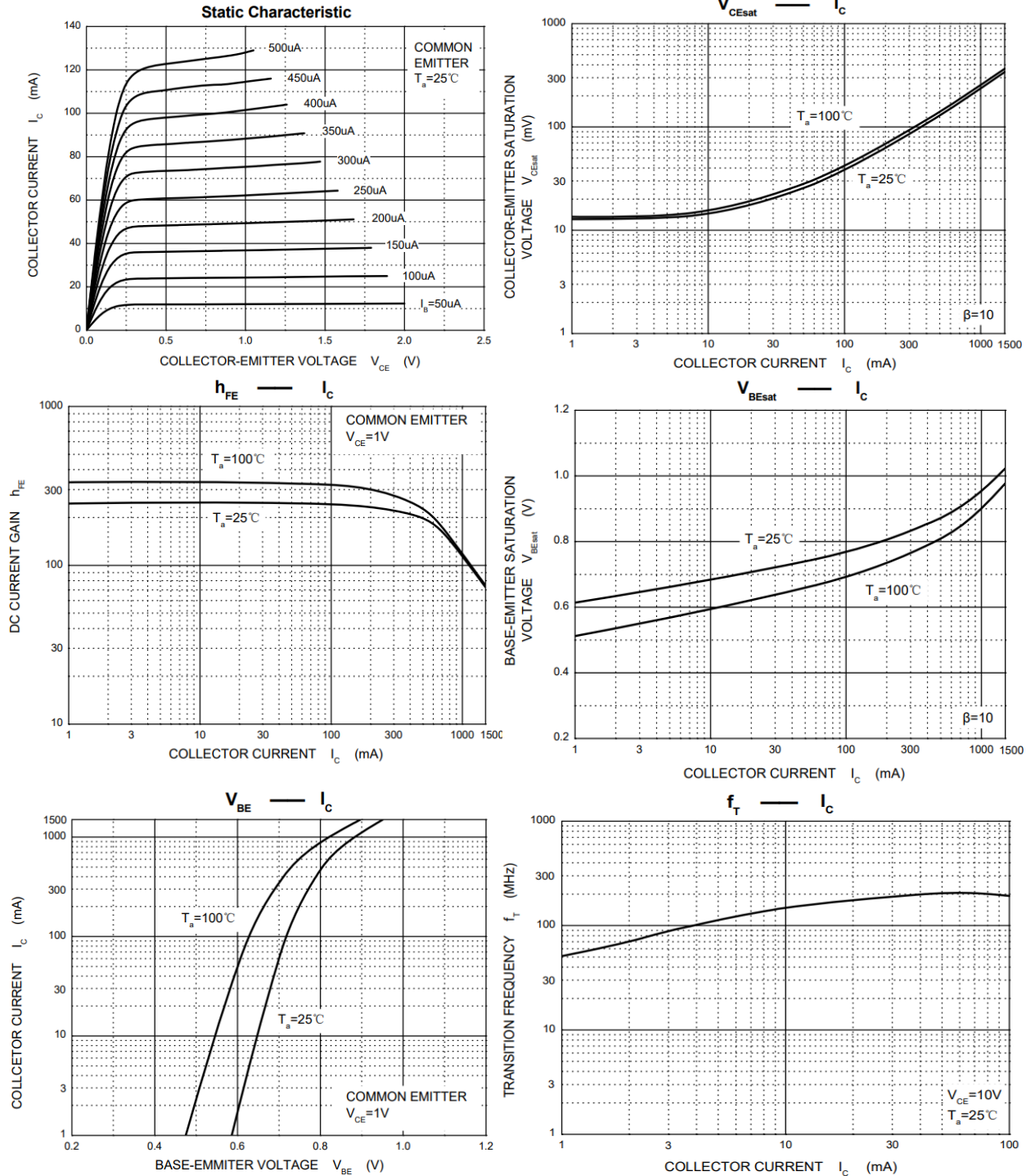
6. ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Condition	Min	Max	Unit
Collector - Emitter Breakdown Voltage	$V_{(BR)CE0}$	$I_C = 0.1\text{mA}$, $I_B = 0$	25		V
Collector - Base Breakdown Voltage	$V_{(BR)CB0}$	$I_C = 0.1\text{mA}$, $I_E = 0$	40		V
Emitter - Base Breakdown Voltage	$V_{(BR)EB0}$	$I_E = 0.1\text{mA}$, $I_C = 0$	5		V
Collector-Emitter Cutoff Current	I_{CE0}	$V_{CE} = 20\text{ V}$, $I_E = 0$		100	nA
Collector Cutoff Current	I_{CB0}	$V_{CB} = 40\text{ V}$, $I_B = 0$		100	nA
Emitter cut-off current	I_{EB0}	$V_{EB} = 5\text{ V}$, $I_C = 0$		100	nA
DC current gain	$h_{FE(1)}$	$I_C = 100\text{mA}$, $V_{CE} = 1\text{ V}$	120	400	
DC current gain	$h_{FE(2)}$	$I_C = 800\text{ mA}$, $V_{CE} = 1\text{ V}$	40		
Collector-Emitter Saturation voltage	$V_{CE(sat)}$	$I_C = 800\text{mA}$, $I_B = 80\text{mA}$		0.5	V
Base - Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 800\text{mA}$, $I_B = 80\text{ mA}$		1.2	V
Transition frequency	f_T	$V_{CE} = 10\text{V}$, $I_C = 50\text{mA}$, $f = 30\text{MHz}$	100		MHz

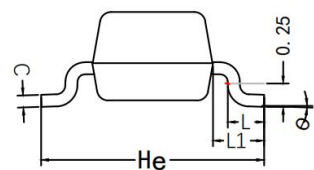
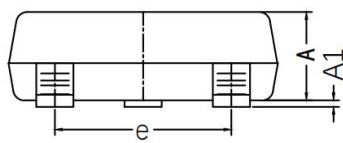
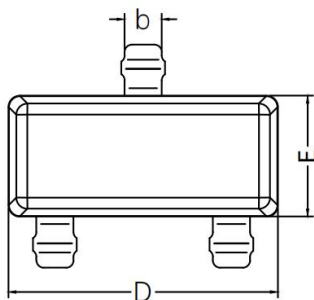
7.

RANK	L	H	J
RANGE	120-200	200-350	300-400

8. ELECTRICAL CHARACTERISTICS CURVES

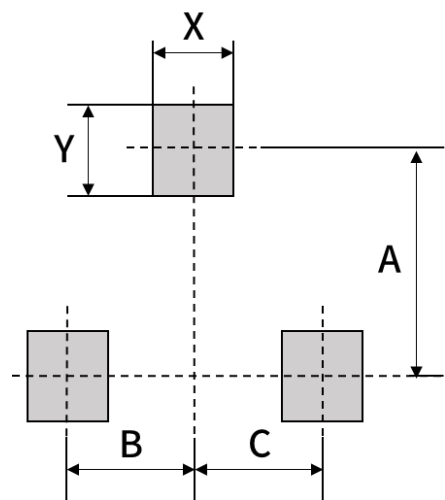


9. OUTLINE AND DIMENSIONS



DIM	MIN	NOR	MAX
A	0.85	0.95	1.05
A1	0.01	0.06	0.10
b	0.36	0.44	0.52
c	0.09	0.13	0.18
D	2.80	2.90	3.10
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.40	0.50
L1	0.35	0.50	0.65
He	2.10	2.35	2.50
θ	0°	—	10°
All Dimensions in mm			

10. SUGGESTED PAD LAYOUT



SOT23		
DIM	mm	inch
A	2.00	0.079
B	0.95	0.037
C	0.95	0.037
X	0.80	0.031
Y	0.90	0.035